# BSP16T1G

## **High Voltage Transistors**

## **PNP Silicon**

### Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-300	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-350	Vdc
Emitter-Base Voltage	$V_{\text{EBO}}$	-6.0	Vdc
Collector Current	۱ <sub>C</sub>	-100	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C (Note 1)	P <sub>D</sub>	1.5	W
Storage Temperature Range	P <sub>D</sub>	-65 to +150	°C
Junction Temperature	TJ	150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

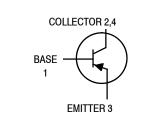
1. Device mounted on a glass epoxy printed circuit board 1.575 in x 1.575 in x 0.059 in; mounting pad for the collector lead min. 0.93 sq. in.

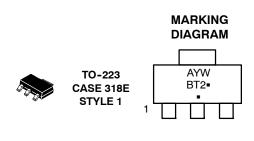


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### PNP SILICON HIGH VOLTAGE TRANSISTOR SURFACE MOUNT





А	= Assembly Location		
Y	= Year		
W	= Work Week		
BT2	=Device Code		
-	= Pb-Free Package		
(Note: Microdot may be in either location)			

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BSP16T1G	TO-223 (Pb-Free)	1000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### BSP16T1G

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ( $I_C = -50 \text{ mAdc}, I_B = 0, L = 25 \text{ mH}$ )	V <sub>(BR)CEO</sub>	-300	-	Vdc
Collector – Base Breakdown Voltage $(I_{C} = -100 \ \mu Adc, I_{E} = 0)$	V <sub>(BR)CBO</sub>	-300	-	Vdc
Collector-Emitter Cutoff Current ( $V_{CE} = -250 \text{ Vdc}, I_B = 0$ )	I <sub>CES</sub>	-	-50	μAdc
Collector-Base Cutoff Current ( $V_{CB} = -280$ Vdc, $I_E = 0$ )	I <sub>CBO</sub>	-	-1.0	μAdc
Emitter-Base Cutoff Current ( $V_{EB} = -6.0 \text{ Vdc}, I_{C} = 0$ )	I <sub>EBO</sub>	-	-20	μAdc
ON CHARACTERISTICS		*	•	•
DC Current Gain (V <sub>CE</sub> = - 10 Vdc, I <sub>C</sub> = -50 mAdc)	h <sub>FE</sub>	30	120	-
Collector-Emitter Saturation Voltage $(I_{C} = -50 \text{ mAdc}, I_{B} = -5.0 \text{ mAdc})$	V <sub>CE(sat)</sub>	-	- 2.0	Vdc
DYNAMIC CHARACTERISTICS	-	-	-	-
Current Gain – Bandwidth Product (V <sub>CE</sub> = -10 Vdc, I <sub>C</sub> = -10 mAdc, f = 30 MHz)	f <sub>T</sub>	15	-	MHz
Collector-Base Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	15	pF

DATE 02 OCT 2018

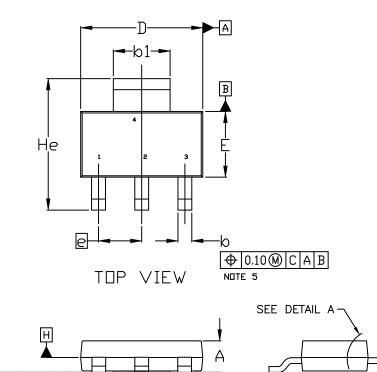




SCALE 1:1

0.10 C

A1



-11

SIDE VIEW

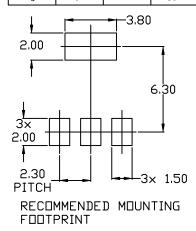
DETAIL A

NDTES:

SOT-223 (TO-261) CASE 318E-04 ISSUE R

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. ALLS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST PDINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS			
DIM	MIN.	NDM.	MAX.	
A	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
b	0.60	0.75	0.89	
b1	2.90	3.06	3.20	
с	0.24	0.29	0.35	
D	6.30	6.50	6.70	
E	3.30	3.50	3.70	
e	2.30 BSC			
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0*		10*	



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#### DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	Style 9: Pin 1. Input 2. Ground 3. Logic 4. Ground	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	Style 12: Pin 1. Input 2. Output 3. NC 4. Output	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

### GENERIC MARKING DIAGRAM\*



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package
- (Note: Microdot may be in either location) \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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